

RJK2017DPE

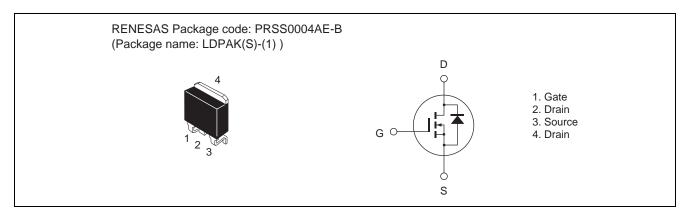
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1589-0400 Rev.4.00 Dec 02, 2009

Features

- Low on-resistance $R_{DS(on)}=0.036~\Omega~typ.~(at~I_D=22.5~A,~V_{GS}=10~V,~Ta=25~^{\circ}C)$
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	45	А
Drain peak current	I _{D (pulse)} Note1	135	А
Body-drain diode reverse drain current	I _{DR}	45	Α
Body-drain diode reverse drain peak current	I _{DR} (pulse)	135	Α
Avalanche current	I _{AP} Note3	12	Α
Avalanche energy	E _{AR} Note3	9.6	mJ
Channel dissipation	Pch Note2	100	W
Channel to case thermal impedance	θch-c	1.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

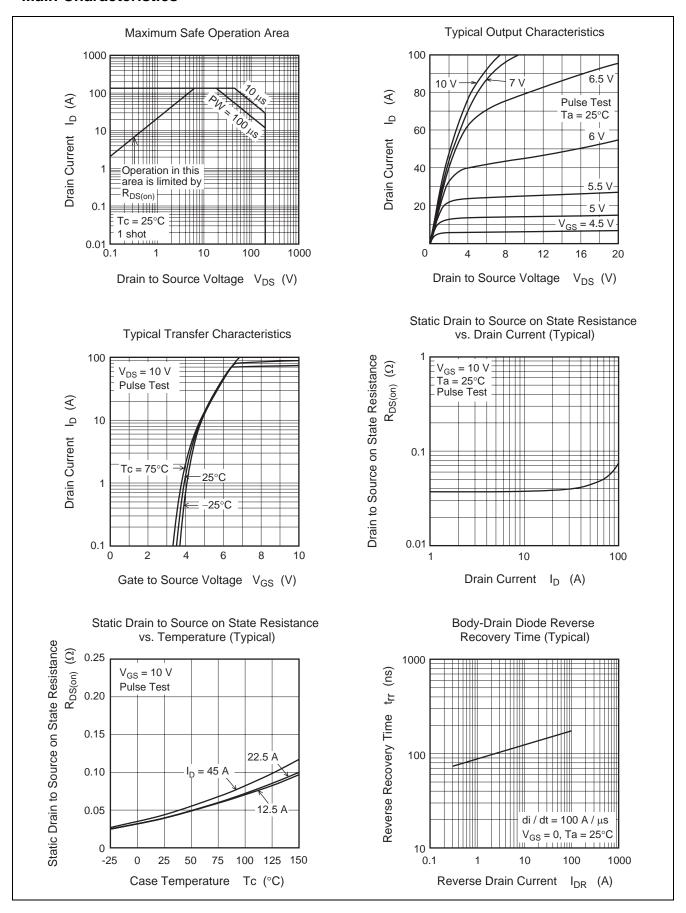
Electrical Characteristics

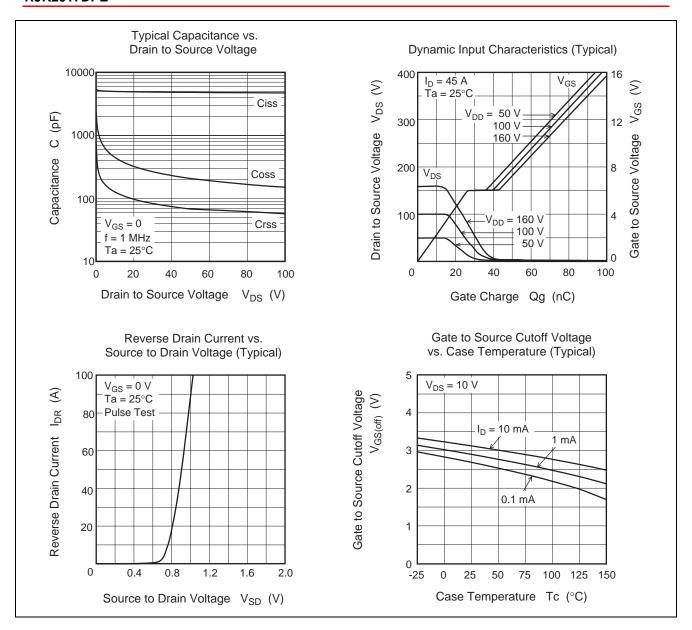
 $(Ta = 25^{\circ}C)$

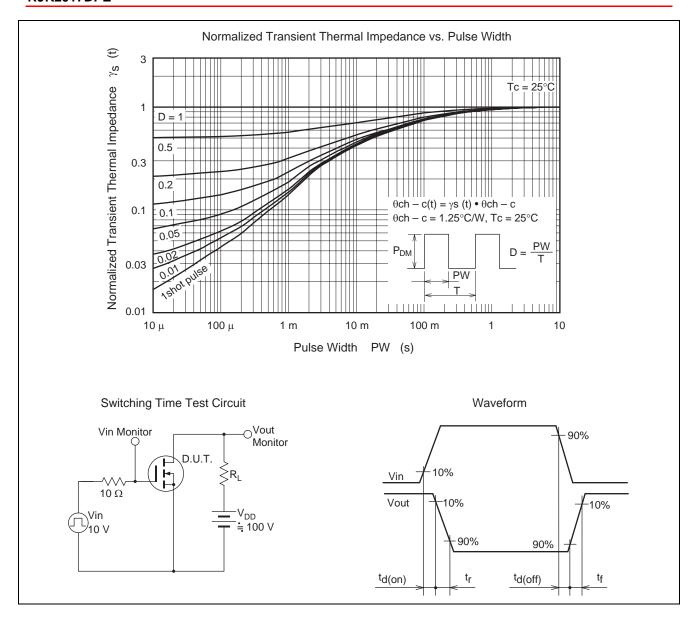
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	V _{DS} = 200 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2	_	4	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	0.036	0.047	Ω	$I_D = 22.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance						
Input capacitance	Ciss	_	4800	_	pF	V _{DS} = 25 V
Output capacitance	Coss		290	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	90	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	50	_	ns	I _D = 22.5 A
Rise time	t _r	_	40	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	95	_	ns	$R_L = 4.5 \Omega$
Fall time	t _f	_	40	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	66	_	nC	V _{DD} = 160 V
Gate to source charge	Qgs	_	26	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd		16	_	nC	I _D = 45 A
Body-drain diode forward voltage	V_{DF}	_	0.88	1.35	V	$I_F = 45 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	150	_	ns	I _F = 45 A, V _{GS} = 0
						di _F /dt = 100 A/μs

Notes: 4. Pulse test

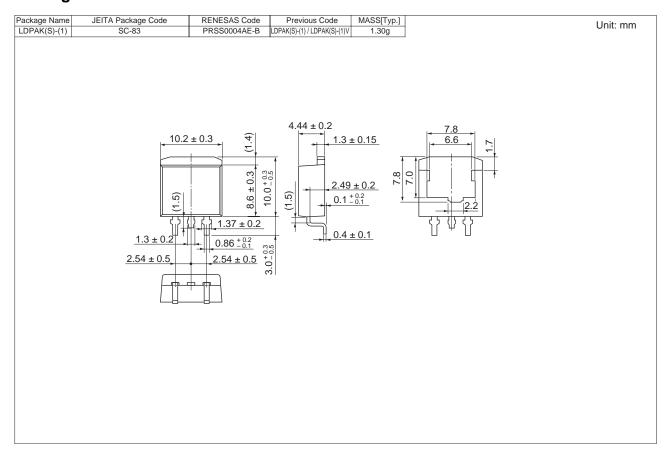
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2017DPE-00-J3	1000 pcs	Taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510